

N-channel dual gate MOS-FETs

BF904; BF904R

FEATURES

- Specially designed for use at 5 V supply voltage
- Short channel transistor with high transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Superior cross-modulation performance during AGC.

APPLICATIONS

- VHF and UHF applications with 3 to 7 V supply voltage such as television tuners and professional communications equipment.

DESCRIPTION

Enhancement type field-effect transistor in a plastic microminiature SOT143B and SOT143R package. The transistor consists of an amplifier MOS-FET with source

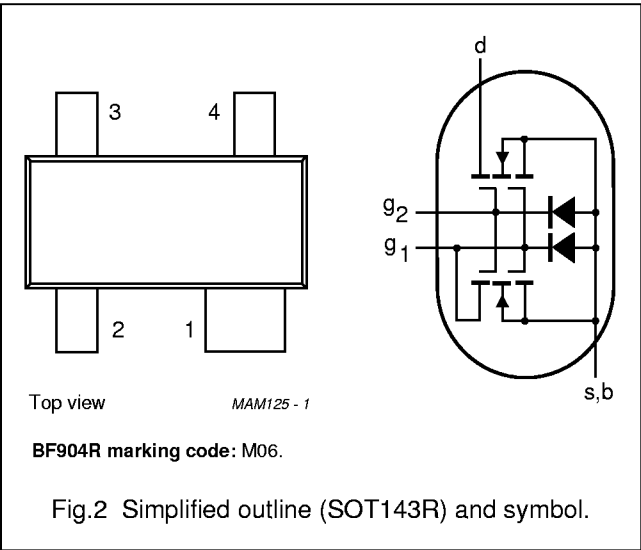
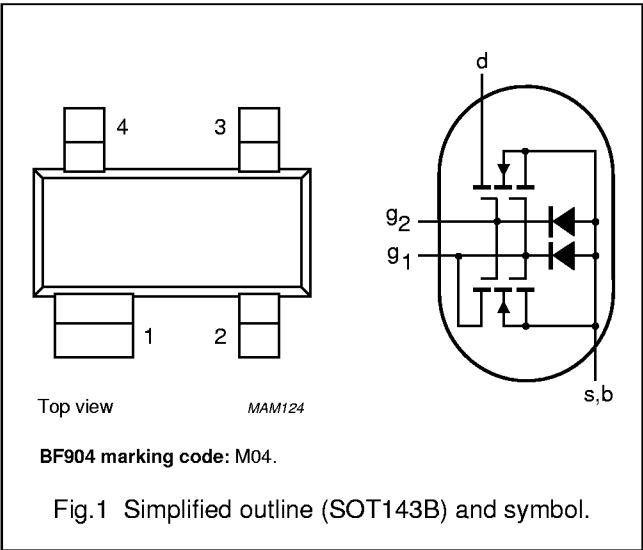
and substrate interconnected and an internal bias circuit to ensure good cross-modulation performance during AGC.

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g ₂	gate 2
4	g ₁	gate 1



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{DS}	drain-source voltage		—	—	7	V
I _D	drain current		—	—	30	mA
P _{tot}	total power dissipation		—	—	200	mW
T _j	operating junction temperature		—	—	150	°C
y _{fs}	forward transfer admittance		22	25	30	mS
C _{ig1-s}	input capacitance at gate 1		—	2.2	2.6	pF
C _{rs}	reverse transfer capacitance	f = 1 MHz	—	25	35	fF
F	noise figure	f = 800 MHz	—	2	—	dB

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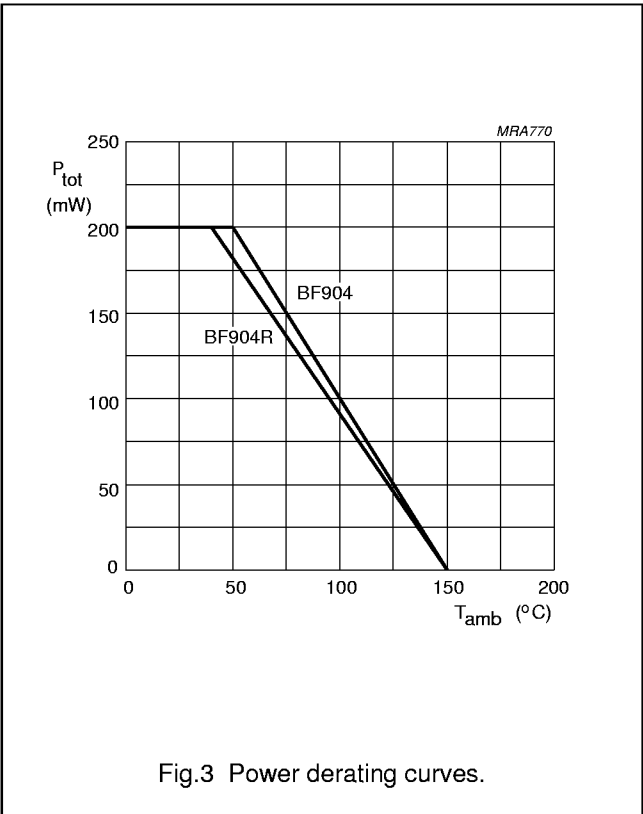
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage		–	7	V
I _D	drain current		–	30	mA
I _{G1}	gate 1 current		–	±10	mA
I _{G2}	gate 2 current		–	±10	mA
P _{tot}	total power dissipation	see Fig.3			
	BF904	T _{amb} ≤ 50 °C; note 1	–	200	mW
	BF904R	T _{amb} ≤ 40 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	operating junction temperature		–	150	°C

Note

- 1. Device mounted on a printed-circuit board.



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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1		
	BF904		500	K/W
	BF904R		550	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 2		
	BF904	$T_s = 92\ ^\circ\text{C}$	290	K/W
	BF904R	$T_s = 78\ ^\circ\text{C}$	360	K/W

Notes

1. Device mounted on a printed-circuit board.
2. T_s is the temperature at the soldering point of the source lead.

STATIC CHARACTERISTICS

$T_j = 25\ ^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$; $I_{G1-S} = 10\ \text{mA}$	6	15	V
$V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$; $I_{G2-S} = 10\ \text{mA}$	6	15	V
$V_{(F)S-G1}$	forward source-gate 1 voltage	$V_{G2-S} = V_{DS} = 0$; $I_{S-G1} = 10\ \text{mA}$	0.5	1.5	V
$V_{(F)S-G2}$	forward source-gate 2 voltage	$V_{G1-S} = V_{DS} = 0$; $I_{S-G2} = 10\ \text{mA}$	0.5	1.5	V
$V_{G1-S(th)}$	gate 1-source threshold voltage	$V_{G2-S} = 4\ \text{V}$; $V_{DS} = 5\ \text{V}$; $I_D = 20\ \mu\text{A}$	0.3	1	V
$V_{G2-S(th)}$	gate 2-source threshold voltage	$V_{G1-S} = V_{DS} = 5\ \text{V}$; $I_D = 20\ \mu\text{A}$	0.3	1.2	V
I_{DSX}	drain-source current	$V_{G2-S} = 4\ \text{V}$; $V_{DS} = 5\ \text{V}$; $R_{G1} = 120\ \text{k}\Omega$; note 1	8	13	mA
I_{G1-SS}	gate 1 cut-off current	$V_{G2-S} = V_{DS} = 0$; $V_{G1-S} = 5\ \text{V}$	—	50	nA
I_{G2-SS}	gate 2 cut-off current	$V_{G1-S} = V_{DS} = 0$; $V_{G2-S} = 5\ \text{V}$	—	50	nA

Note

1. R_{G1} connects gate 1 to $V_{GG} = 5\ \text{V}$; see Fig.20.

DYNAMIC CHARACTERISTICS

Common source; $T_{amb} = 25\ ^\circ\text{C}$; $V_{DS} = 5\ \text{V}$; $V_{G2-S} = 4\ \text{V}$; $I_D = 10\ \text{mA}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ y_{fs} $	forward transfer admittance	pulsed; $T_j = 25\ ^\circ\text{C}$	22	25	30	mS
C_{ig1-s}	input capacitance at gate 1	$f = 1\ \text{MHz}$	—	2.2	2.6	pF
C_{ig2-s}	input capacitance at gate 2	$f = 1\ \text{MHz}$	1	1.5	2	pF
C_{os}	drain-source capacitance	$f = 1\ \text{MHz}$	1	1.3	1.6	pF
C_{rs}	reverse transfer capacitance	$f = 1\ \text{MHz}$	—	25	35	fF
F	noise figure	$f = 200\ \text{MHz}$; $G_S = 2\ \text{mS}$; $B_S = B_{Sopt}$	—	1	1.5	dB
		$f = 800\ \text{MHz}$; $G_S = G_{Sopt}$; $B_S = B_{Sopt}$	—	2	2.8	dB

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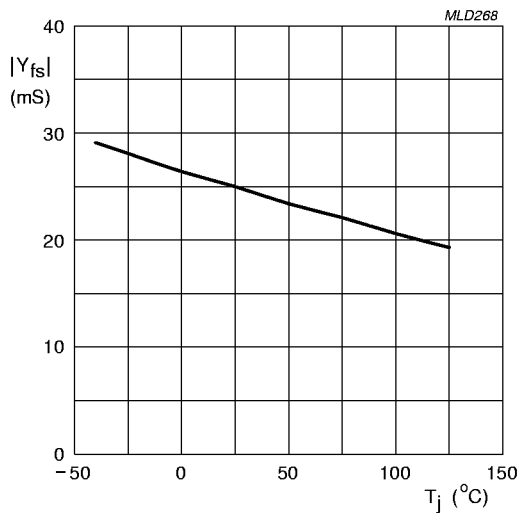
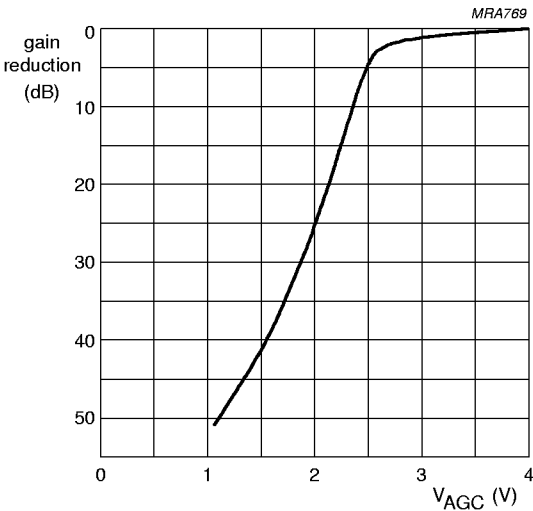
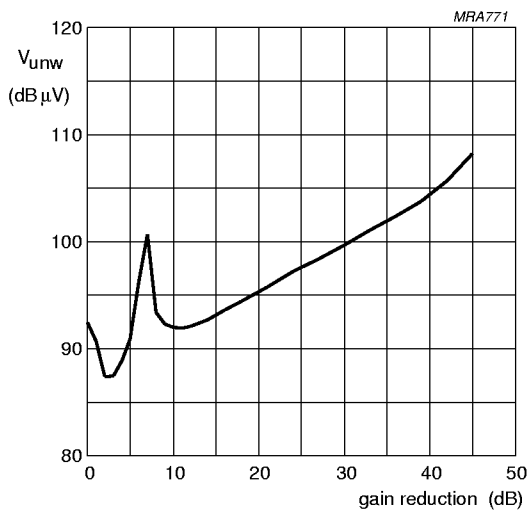


Fig.4 Transfer admittance as a function of the junction temperature; typical values.



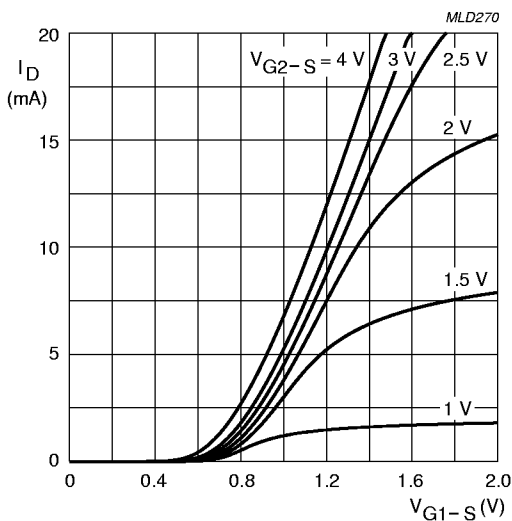
$f = 50$ MHz.

Fig.5 Typical gain reduction as a function of the AGC voltage.



$V_{DS} = 5$ V; $V_{GG} = 5$ V; $f_w = 50$ MHz.
 $f_{unw} = 60$ MHz; $T_{amb} = 25$ °C; $R_{G1} = 120$ k Ω .

Fig.6 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; see Fig.20.

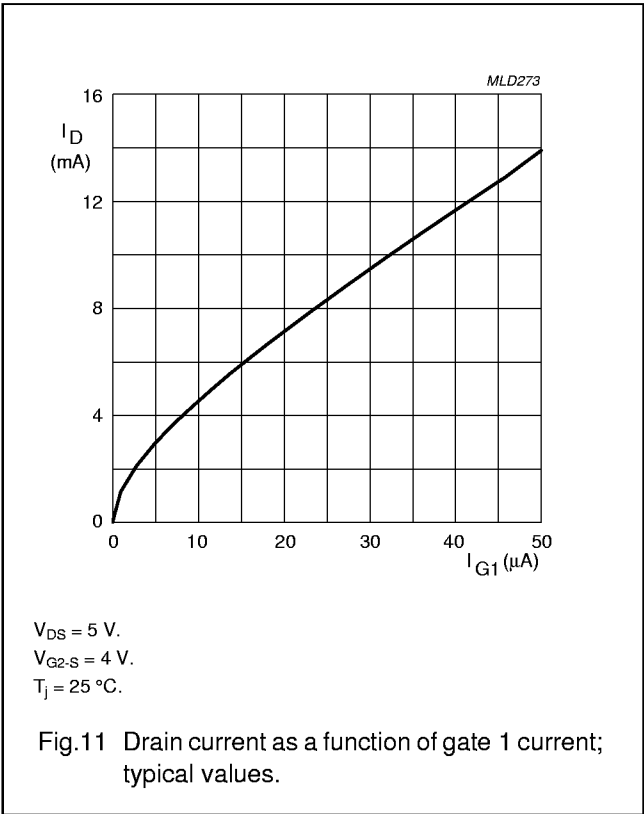
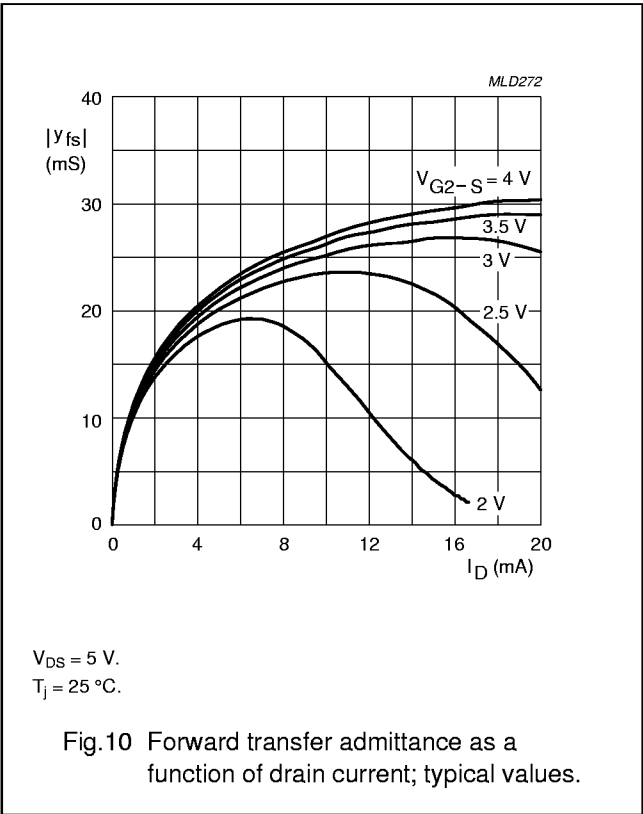
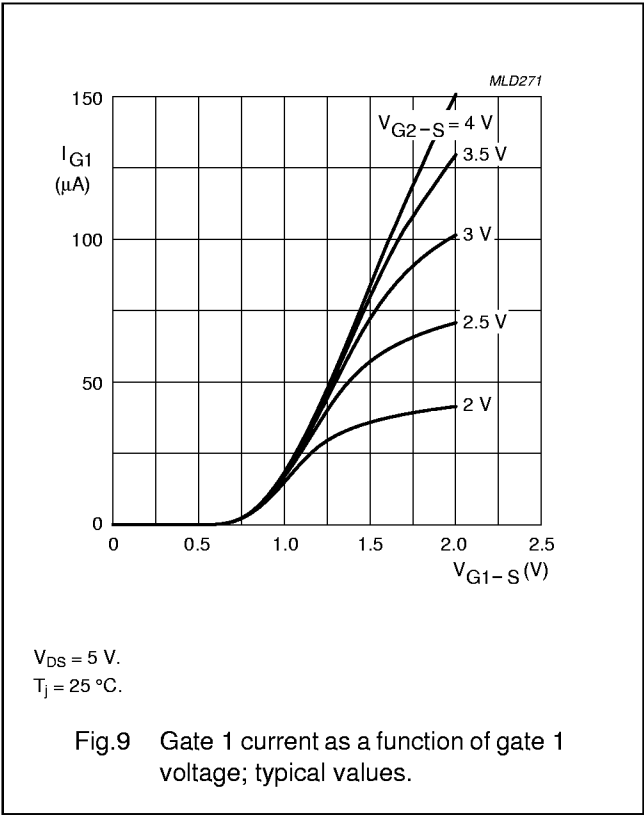
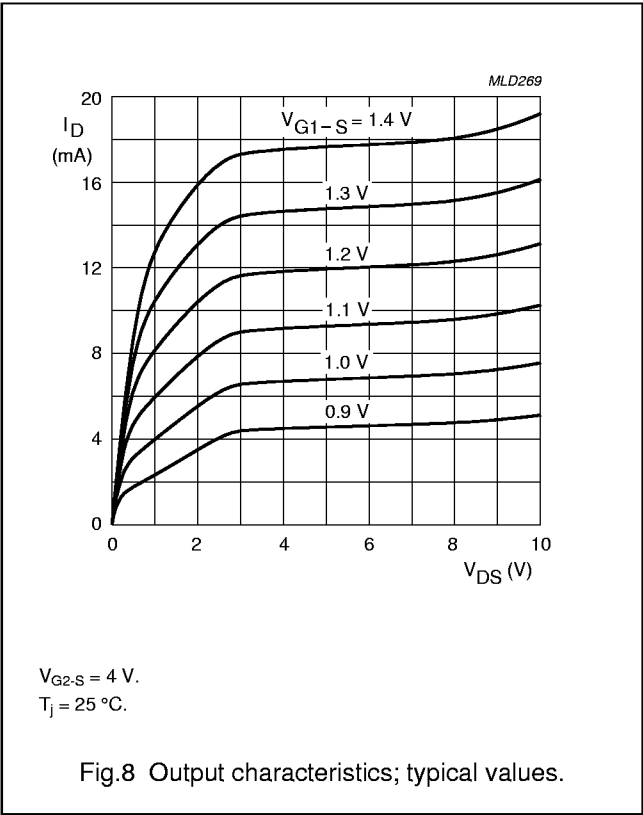


$V_{DS} = 5$ V.
 $T_j = 25$ °C.

Fig.7 Transfer characteristics; typical values.

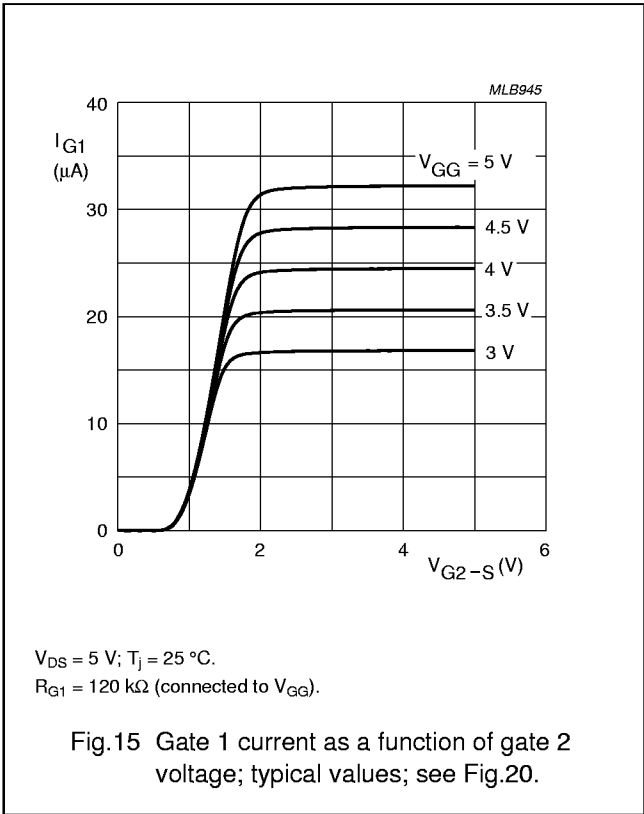
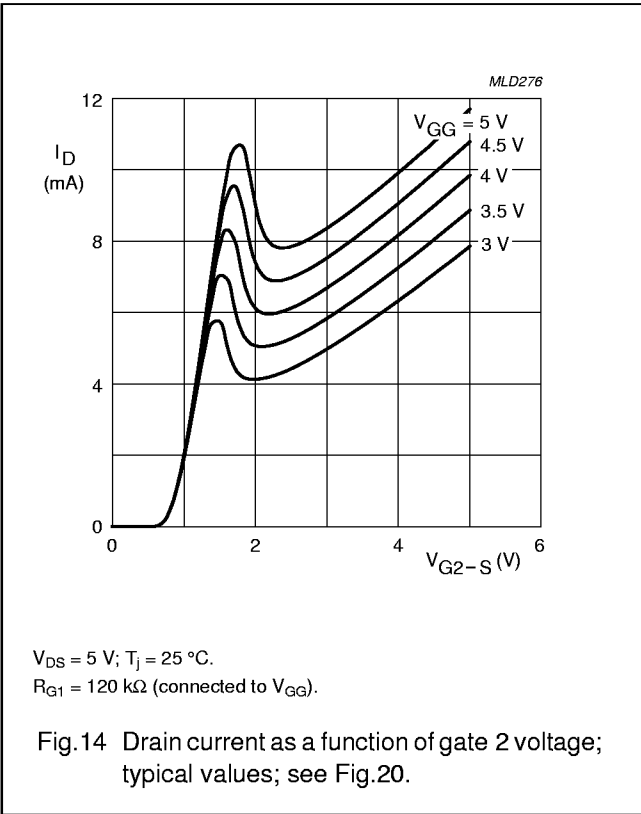
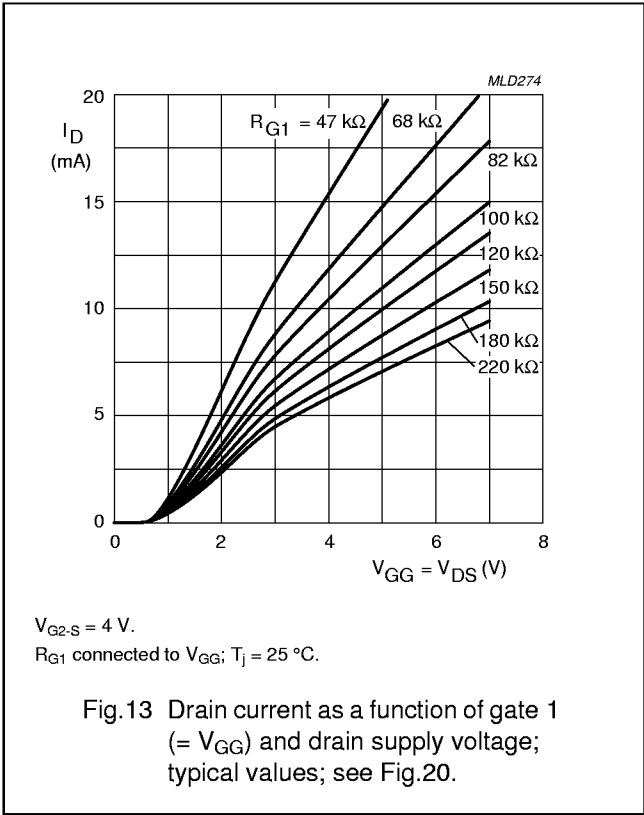
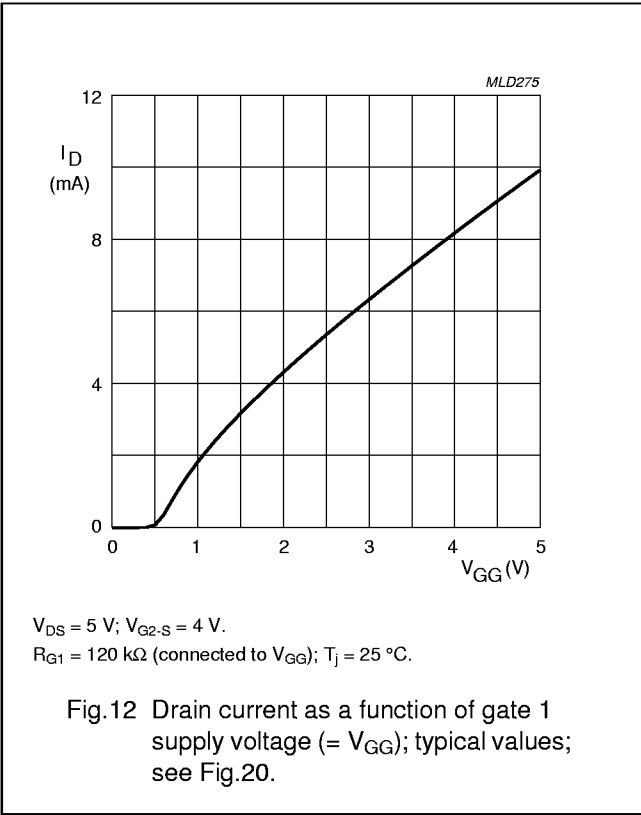
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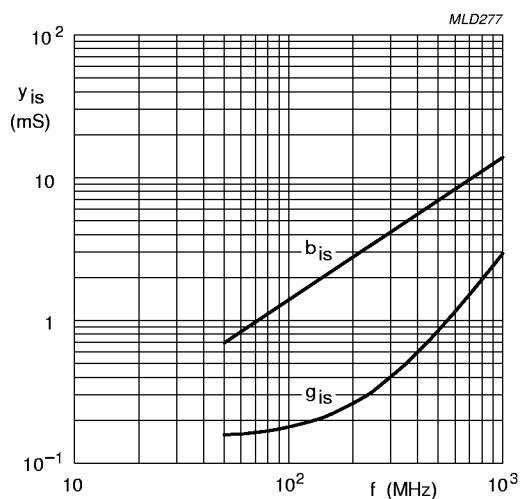
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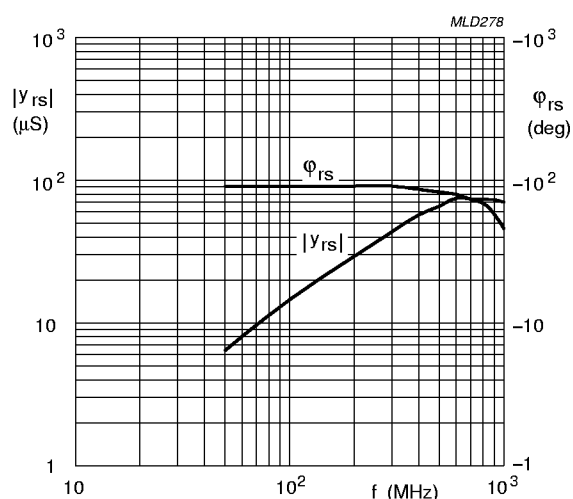
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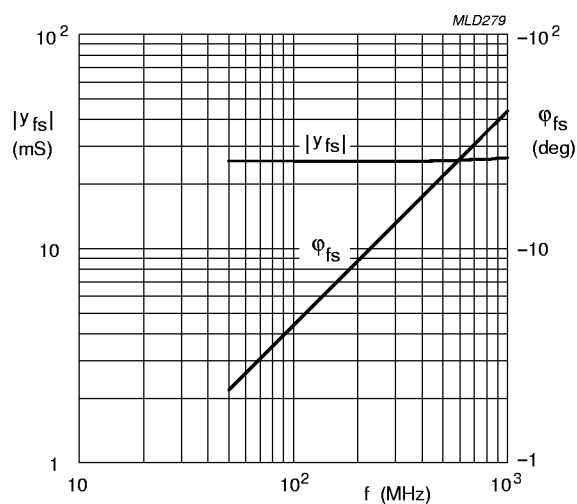
$V_{DS} = 5$ V; $V_{G2} = 4$ V.
 $I_D = 15$ mA; $T_{amb} = 25$ °C.

Fig. 16 Input admittance as a function of frequency; typical values.



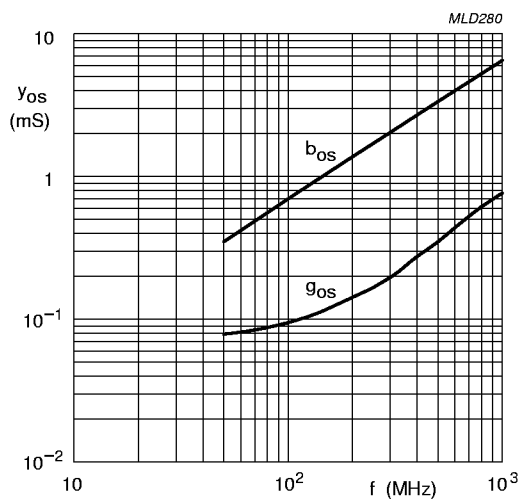
$V_{DS} = 5$ V; $V_{G2} = 4$ V.
 $I_D = 15$ mA; $T_{amb} = 25$ °C.

Fig. 17 Reverse transfer admittance and phase as a function of frequency; typical values.



$V_{DS} = 5$ V; $V_{G2} = 4$ V.
 $I_D = 15$ mA; $T_{amb} = 25$ °C.

Fig. 18 Forward transfer admittance and phase as a function of frequency; typical values.



$V_{DS} = 5$ V; $V_{G2} = 4$ V.
 $I_D = 15$ mA; $T_{amb} = 25$ °C.

Fig. 19 Output admittance as a function of frequency; typical values.

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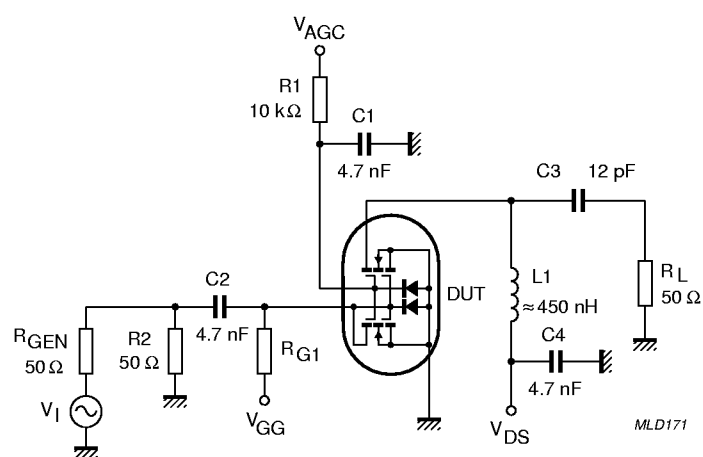


Fig.20 Cross-modulation test set-up.

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Table 1 Scattering parameters: $V_{DS} = 5\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
40	0.989	-3.4	2.420	175.7	0.000	79.9	0.993	-1.6
100	0.985	-8.3	2.414	169.1	0.001	78.3	0.992	-3.9
200	0.976	-16.4	2.368	158.8	0.003	80.3	0.987	-7.8
300	0.958	-24.1	2.301	148.5	0.004	73.7	0.980	-11.4
400	0.942	-32.0	2.251	138.8	0.005	70.7	0.974	-15.2
500	0.918	-39.3	2.170	129.5	0.005	67.2	0.966	-18.7
600	0.899	-46.0	2.080	120.7	0.005	67.8	0.958	-22.2
700	0.876	-52.6	2.001	112.1	0.005	68.6	0.951	-25.5
800	0.852	-58.8	1.924	103.2	0.005	72.9	0.944	-28.9
900	0.823	-64.9	1.829	94.7	0.005	78.7	0.937	-32.1
1000	0.800	-70.9	1.747	86.5	0.005	88.3	0.933	-35.2
1200	0.750	-82.4	1.621	70.7	0.005	120.5	0.928	-41.7
1400	0.719	-92.7	1.535	54.6	0.008	139.8	0.930	-48.4
1600	0.682	-102.5	1.424	39.4	0.010	137.8	0.924	-54.9
1800	0.642	-109.8	1.349	22.5	0.013	156.8	0.928	-62.9
2000	0.602	-116.5	1.283	1.1	0.018	175.1	0.928	-73.1
2200	0.547	-124.9	1.130	-15.1	0.014	172.6	0.887	-81.0
2400	0.596	-128.7	1.018	-49.1	0.040	-163.9	0.837	-95.8
2600	0.682	-132.6	0.979	-79.4	0.077	-164.0	0.778	-109.6
2800	0.771	-142.5	0.804	-116.2	0.120	178.8	0.629	-119.5
3000	0.793	-157.5	0.541	-153.5	0.149	158.3	0.479	-119.9

Table 2 Noise data: $V_{DS} = 5\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$

f (MHz)	F _{min} (dB)	Γ _{opt}		r _n
		(ratio)	(deg)	
800	2.00	0.686	49.6	50.40

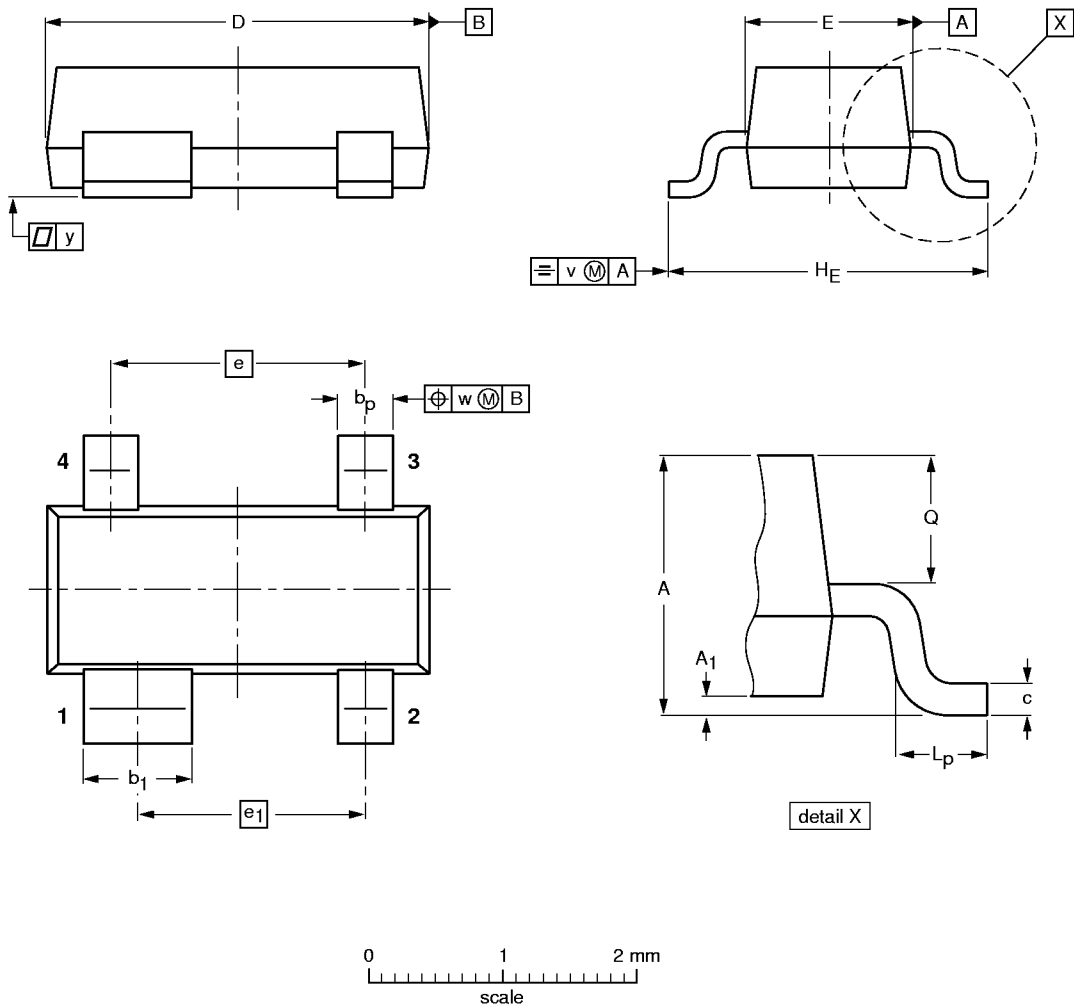
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PACKAGE OUTLINES

Plastic surface mounted package; 4 leads

SOT143B



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

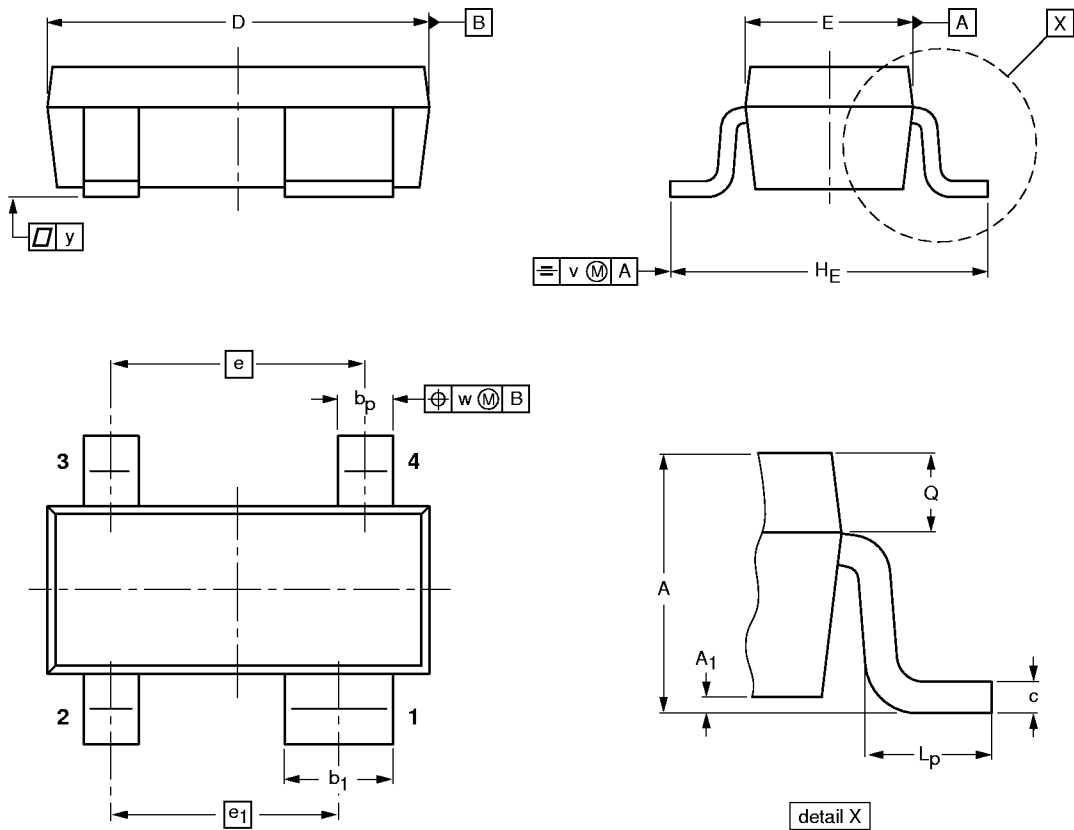
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

N-channel dual gate MOS-FETs

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Plastic surface mounted package; reverse pinning; 4 leads

SOT143R



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.55 0.25	0.45 0.25	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
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SOT143R						97-03-10